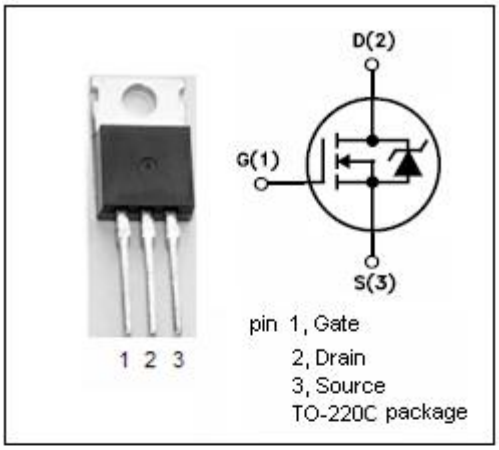
isc N-Channel Mosfet Transistor BUZ80



- **FEATURES**
- High speed switching
- Low $R_{DS(ON)}$
- Easy driver for cost effective application
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

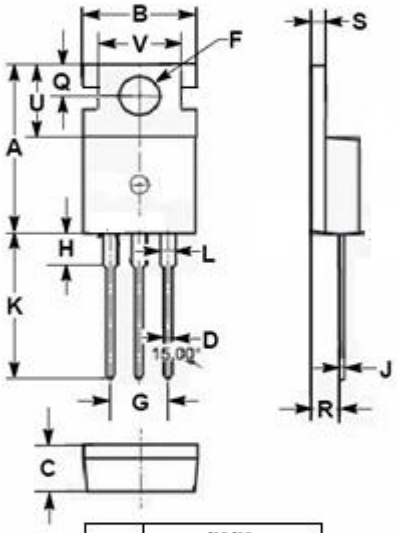
- **DESCRIPTION**
- High current , high speed switching
- Switching mode power supplies
- DC-DC & DC-AC converter

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	800	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=25℃	3.4	A
I_{DM}	Drain Current-Single Plused	13	A
P_{tot}	Total Dissipation@TC=25℃	100	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.25	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D=0.25mA	800			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D=1mA	2.0		4.0	V
V_{SD}	Diode Forward On-voltage	I_S= 6A ;V_{GS}= 0			2.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 1.7A			4	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=800V; V_{GS}= 0			25	μA
Gfs	Forward Transconductance	V_{DS}= 25V； I_D=1.7A	1			S